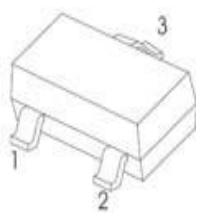
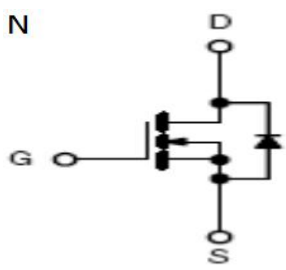
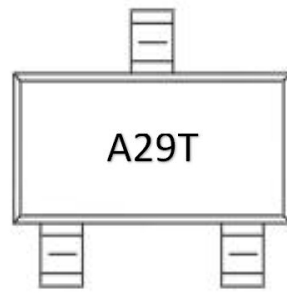
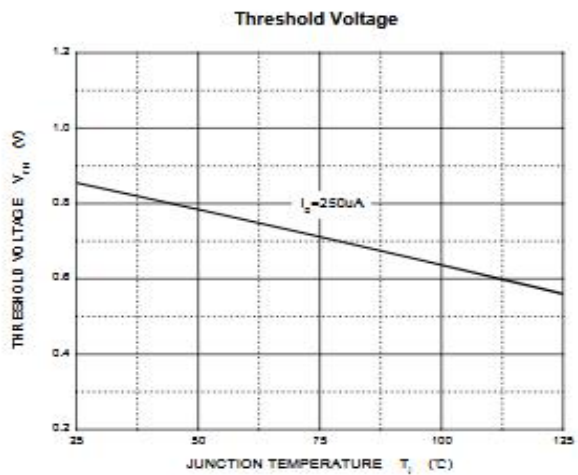
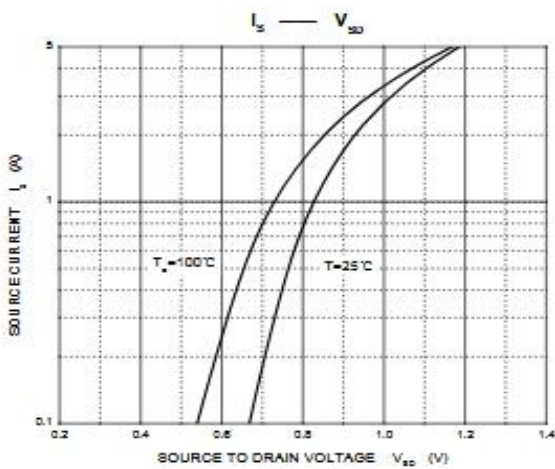
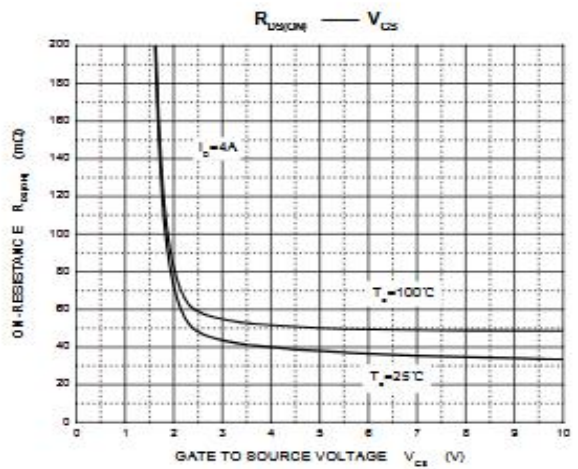
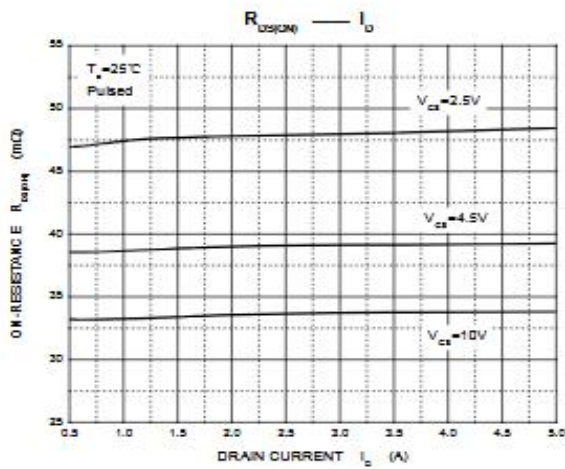
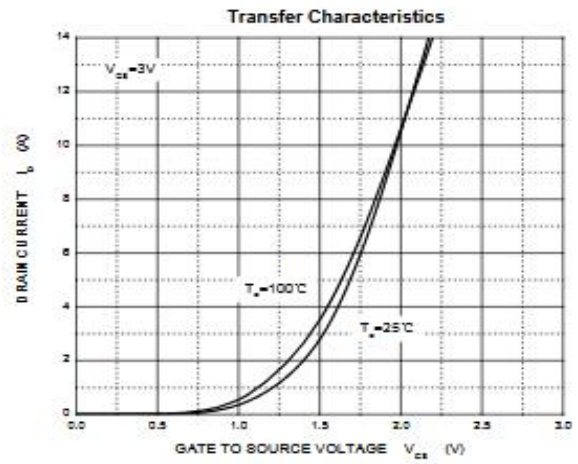
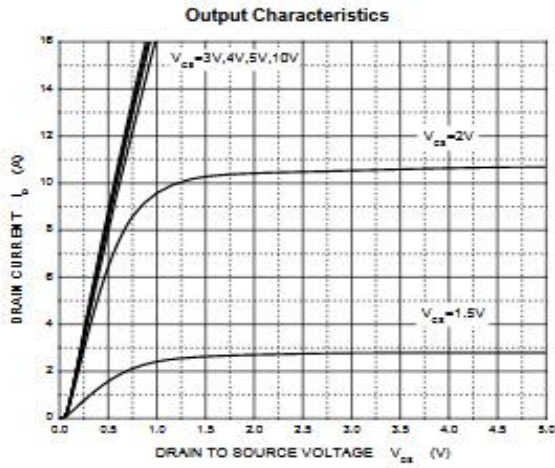


N-Channel 30-V(D-S) MOSFET		SOT-23 Plastic-Encapsulate MOSFETS	
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p style="text-align: center;">Equivalent Circuit</p> 		<p>Features</p> <ul style="list-style-type: none"> ※ TrenchFET Power MOSFET <p>Application</p> <ul style="list-style-type: none"> ※ Load Switch for Portable Devices ※ DC/DC Converter <p>MARKING</p> 	
V(BR)DSS	RDS(on)MAX		ID
30 V	55mΩ @10V		4A
	70mΩ @4.5V		
	110mΩ @2.5V		
Maximum ratings (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	4	A
Pulsed Diode Current	IDM	15	
Continuous Source-Drain Current(Diode Conduction)	IS	0.72	
Power Dissipation	PD	0.35	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	150	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS						
Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250µA	30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = 250µA	0.6	1	1.4	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±12V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 30V, VGS =0V			1	µA
Drain-source on-state resistancea	RDS(on)	VGS = 10V, ID = 0.5A		38	55	mΩ
		VGS = 4.5V, ID = 0.5A		44	70	mΩ
		VGS = 2.5V, ID = 0.5A		52	110	mΩ
Forward transconductancea	gfs	VDS = 4.5V, ID = 4A	8			S
Diode forward voltage	VSD	IS=1A,VGS=0V		0.7	1.3	V
Dynamic						
Input capacitance	Ciss	VDS = 15V,VGS =0V, f=1MHz		390		pF
Output capacitance	Coss			54.5		pF
Reverse transfer capacitanceb	Crss			41		pF
Total gate charge	Qg	VDS = 10V,VGS = 4.5V, ID =-4.5A		11	14	nC
Gate-source charge	Qgs			1.3		nC
Gate-drain charge	Qgd			2.8		nC
Gate resistance	Rg	f=1MHz		3		Ω
Switchingb						
Turn-on delay time	td(on)	VDD= 10V RL=10Ω, ID ≈ 1A, VGEN= 4.5V,Rg=6Ω		3.3		ns
Rise time	tr			1		ns
Turn-off delay time	td(off)			21.7		ns
Fall time	tf			2.1		ns
Drain-source body diode characteristics						
Continuous Source-Drain Diode Current	IS	Tc=25°C			1.2	A
Body Diode Reverse Recovery Time	trr	IF=4A, dI/dt=100A/us		12		ns
Body Diode Reverse Recovery Char	Qrr	IF=4A, dI/dt=100A/us		6.3		nC
Note :						
1. Repetitive Rating : Pulse width limited by maximum junction temperature.						
2. Surface Mounted on FR4 Board, t < 5 sec.						
3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.						
4. Guaranteed by design, not subject to production testing.						

Typical Characteristics:



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)